



# *Readout ASIC of Pair-monitor for ILC*

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Tohoku university

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# Outline

## **1. Introduction**

- International Linear Collider
- Pair-monitor

## **2. Development of the readout ASIC**

- Design and layout
- Operation test

## **3. Pair-monitor with SOI technology**

## **4. Summary**

# **1. Introduction**

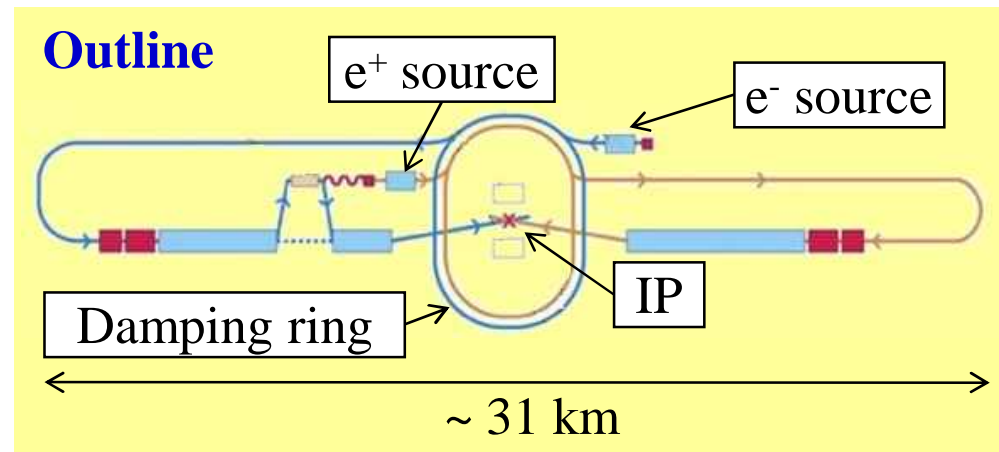
# International Linear Collider

## ILC ( International Linear Collider )

Next generation of the high-energy  $e^+ e^-$  collider

- Purpose

- Study Higgs, new physics ...



- Parameters

- CM energy : 500 GeV ( upgrade to 1 TeV)
- Integrated luminosity :  $2 \times 10^{34} \text{ cm}^{-2} \text{ s}^{-1}$

→ Beam profile monitor is necessary to keep the high luminosity.

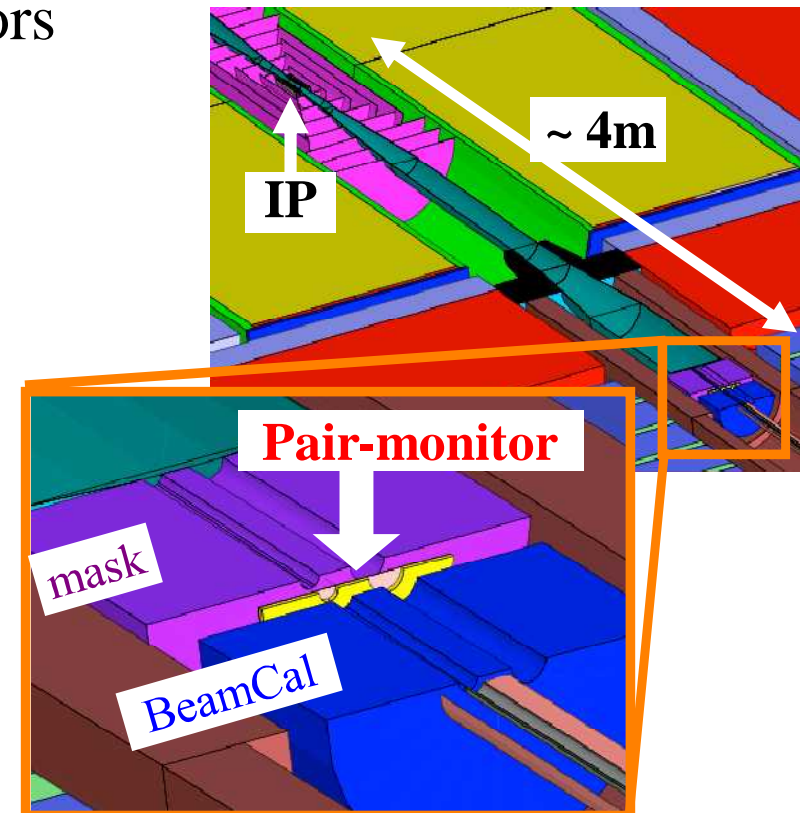
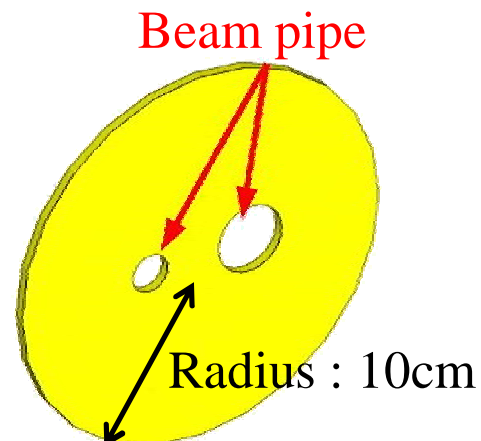
# Pair-monitor

## Requirement to the beam profile monitor

- Measurement accuracy of the beam size :  $< \sim 10\%$ 
  - Beam size :  $(\sigma_x, \sigma_y, \sigma_z) = (639\text{nm}, 5.7\text{nm}, 300\mu\text{m})$
- Quick feed-back of measurement result
- No disturbance of other particle detectors

### → Candidate : Pair-monitor

- Silicon pixel sensor
- Location :  $\sim 4\text{m}$  from IP
- Radius :  $10\text{cm}$

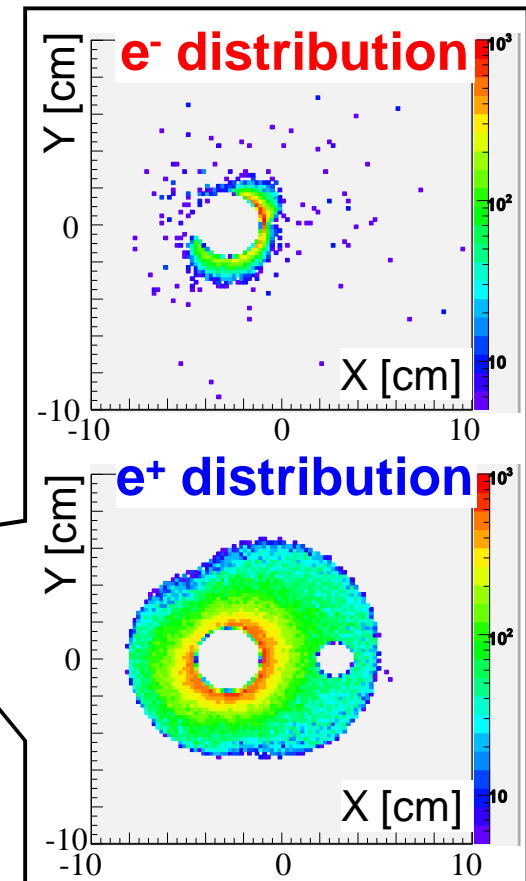
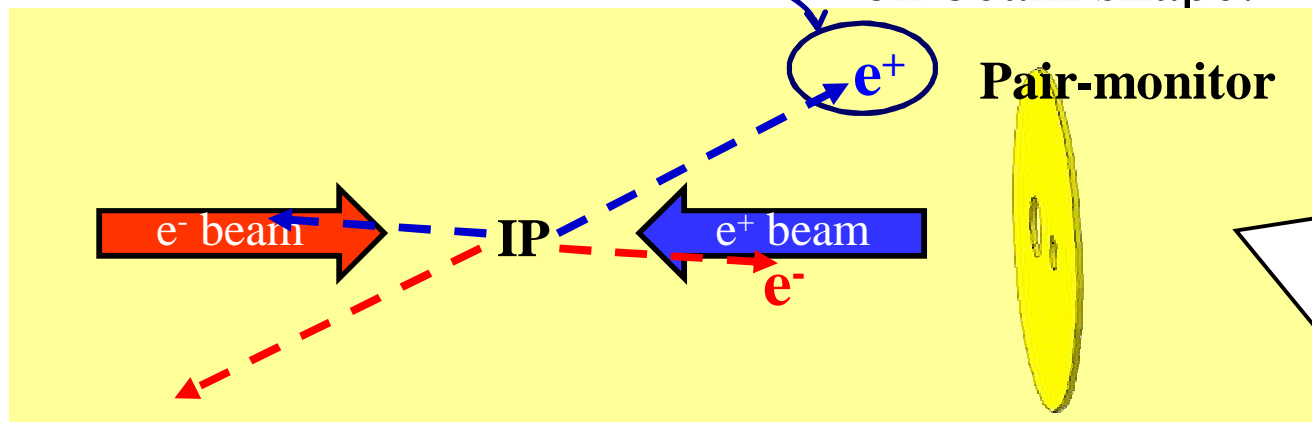


# Beam profile measurement

## Idea of the beam profile measurement

**Pair-monitor measures  $\sigma_x$  and  $\sigma_y$  of the beam at IP, using the hit distribution of the pair B.G.**

- A lot of the pair B.G are created during beam crossing.
- The same charges with respect to the oncoming beam are scattered with large angle.
- The scattered particles have information on beam shape.



→ Tohoku group has developed the pair-monitor.

## **2. Development of readout ASIC**

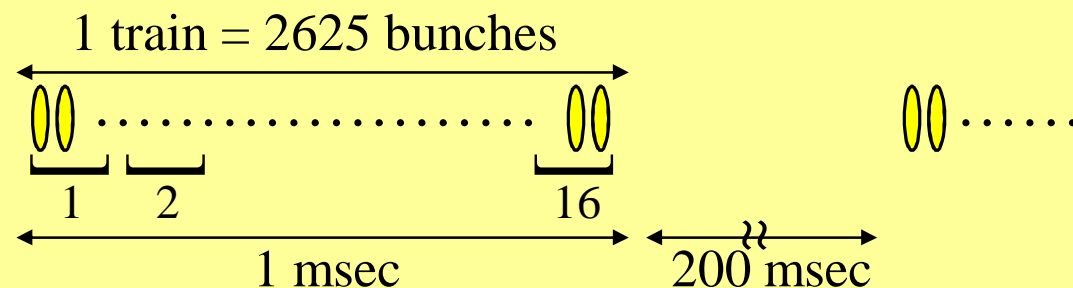
# Development of the readout ASIC

As the first step, readout ASIC was developed.

## Design concept of readout ASIC

- Pair-monitor measures the hit distribution of the pair B.G.
- Measurement is done for 16 parts in one train
  - for the time-dependent measurement.
    - 16 Hit counts are stored at each part.
    - Count rate :  $< 2.5 \text{ MHz} / (400\mu\text{m} \times 400\mu\text{m})$
    - Information of the energy deposit is not necessary.
- Data is read out during inter-train gaps. (  $\sim 200 \text{ msec}$  )

### Beam structure at ILC



→ The prototype readout ASIC was designed to satisfy these concepts.

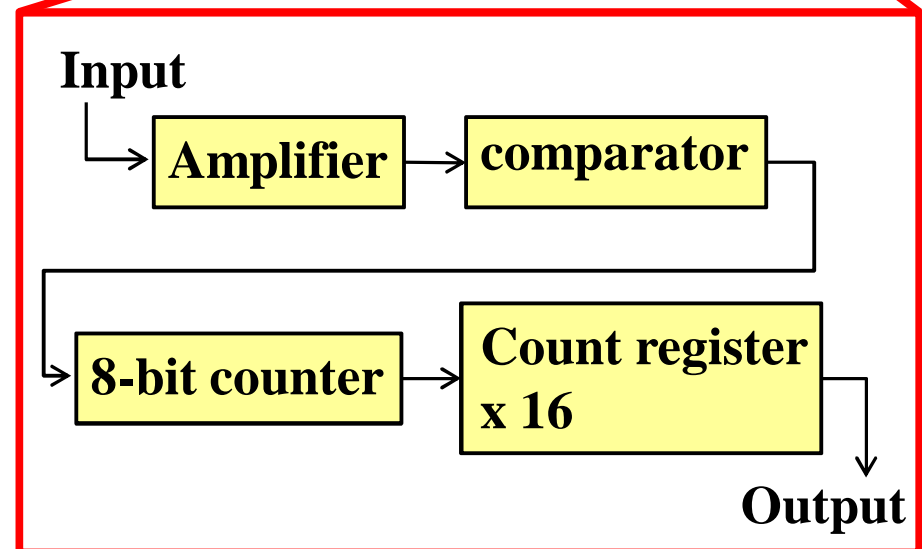
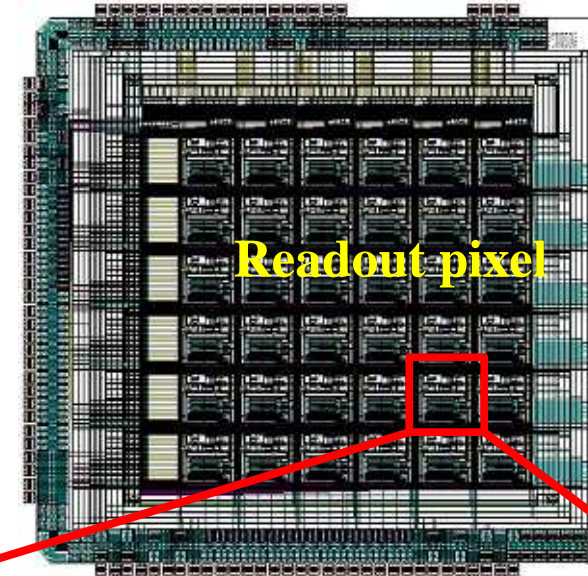


# Design of readout ASIC

## Design of readout ASIC

- 36 (6 x 6) readout pixels
  - Amplifier
  - comparator
  - 8-bit counter
    - to hit a number of hits
  - 16 count-registers
    - to store hit counts
- Shift register
  - to select a pixel from 36 pixels

## Layout of prototype ASIC



# Prototype of Readout ASIC

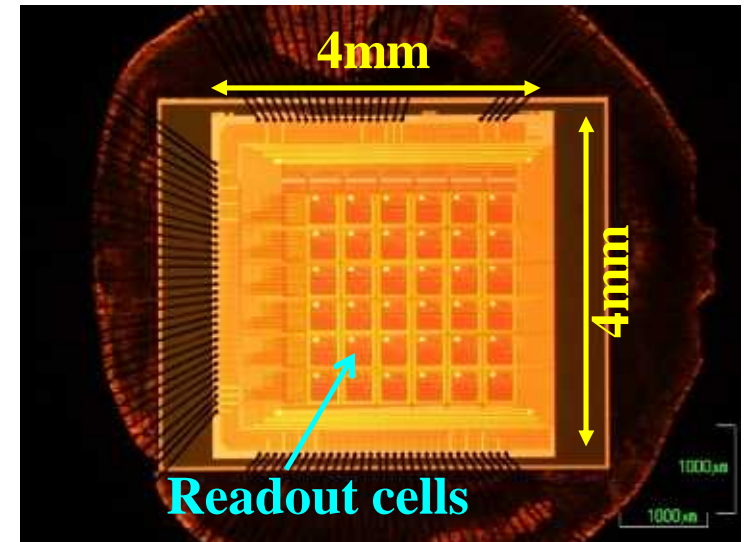
The prototype of the readout ASIC was developed.

## Prototype ASIC

- Production process : 0.25  $\mu\text{m}$  TSMC
- Chip size: 4 x 4mm<sup>2</sup>
- # of pixel : 36 ( = 6x6 )
- Pixel size : 400 x 400  $\mu\text{m}^2$
- Sensor will be bump-bonded to the ASIC.
- The chip was packaged in a PGA144.

→ The 3<sup>rd</sup> production of the readout ASIC  
was done in Oct. 2008.

→ The trouble was found in the 1<sup>st</sup> and 2<sup>nd</sup> production.



**Packaged ASIC**

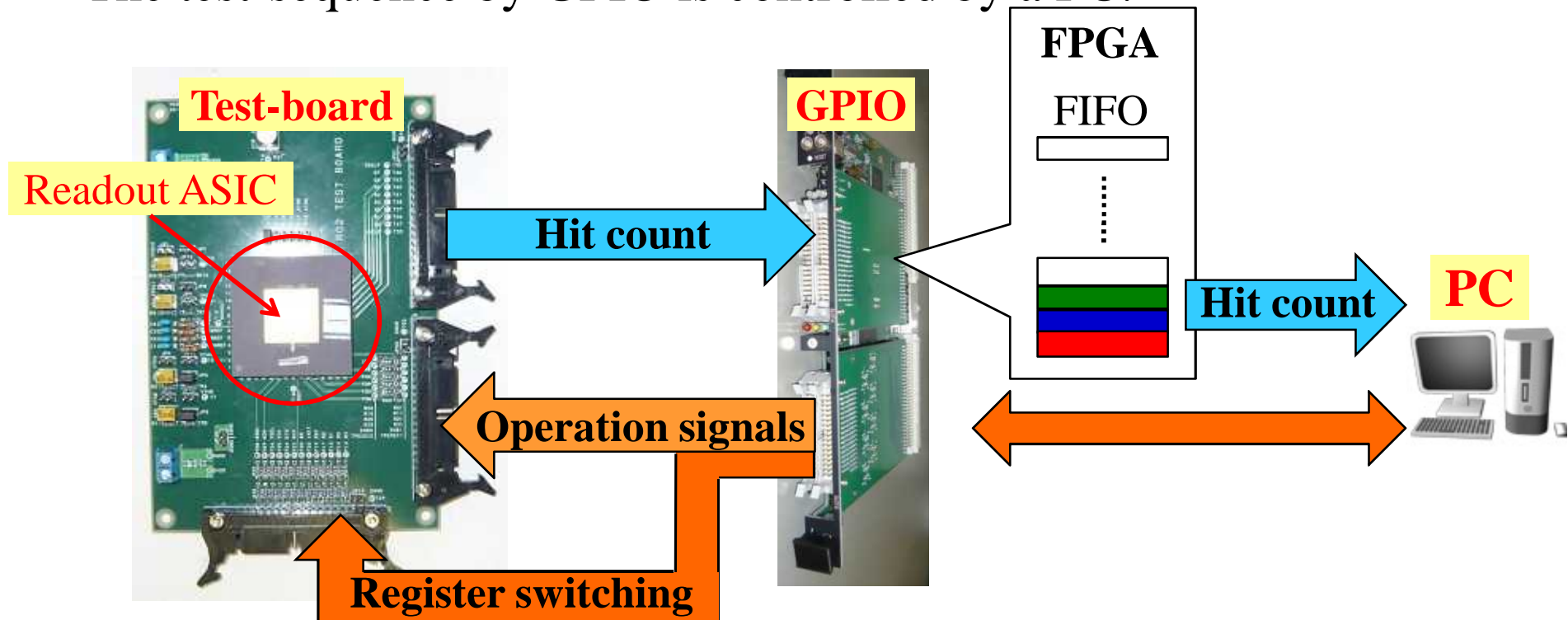


# Test system

The operation test was performed.

## Test system

- GNV-250 module was used for the operation and readout .
  - KEK-VME 6U module
- The test-sequence by GPIO is controlled by a PC.

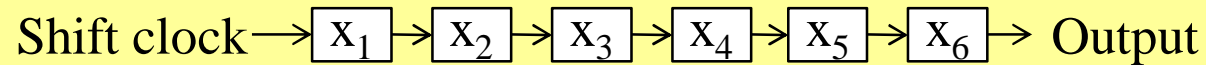


# Problem in the 1<sup>st</sup> production (1)

The 1<sup>st</sup> production of the readout ASIC was done in 2006.

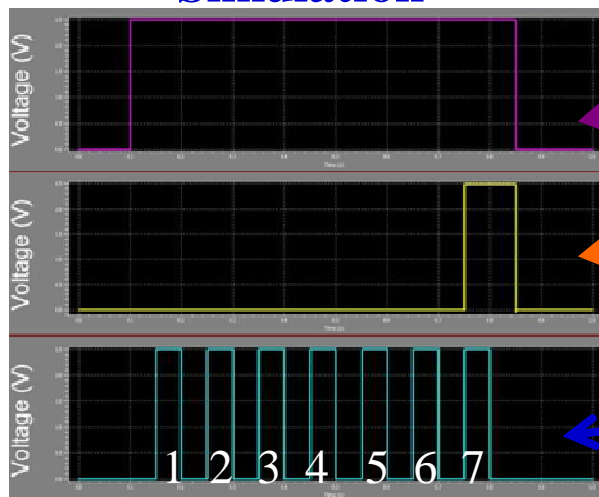
## Problem

- The shift register to select a readout pixel did not work correctly.
  - The readout pixel is selected by the number of the shift clock.



- Output should rise at 7<sup>th</sup> clock, and fall when the shift gate falls.

### Simulation

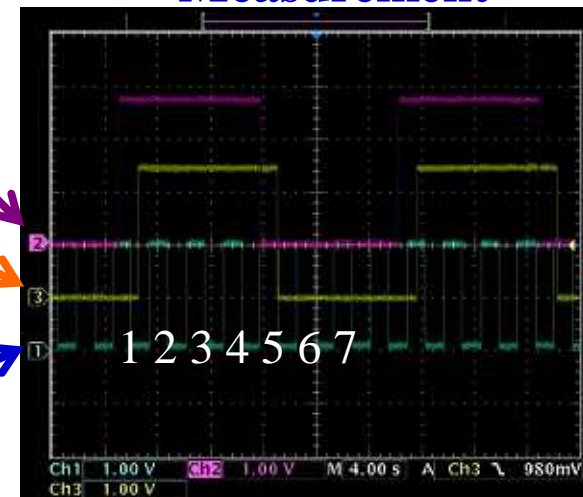


Shift gate

Output from shift register

Shift clock

### Measurement



→ The reason of the problem was investigated.



## Problem in the 1<sup>st</sup> production (2)

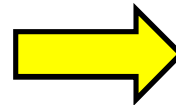
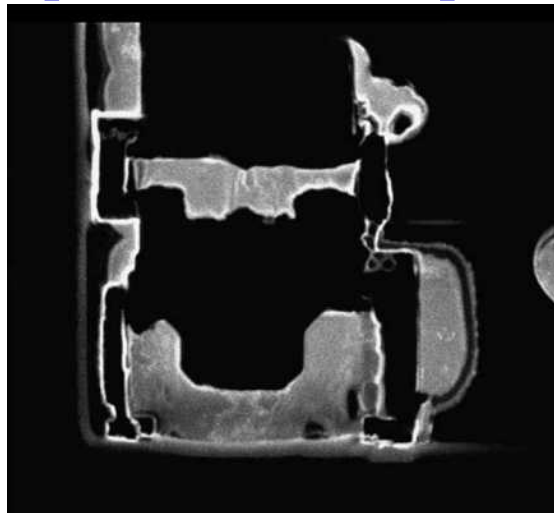
### Reason

- The input register had disconnection.
  - The layout information is not defined in the process library.

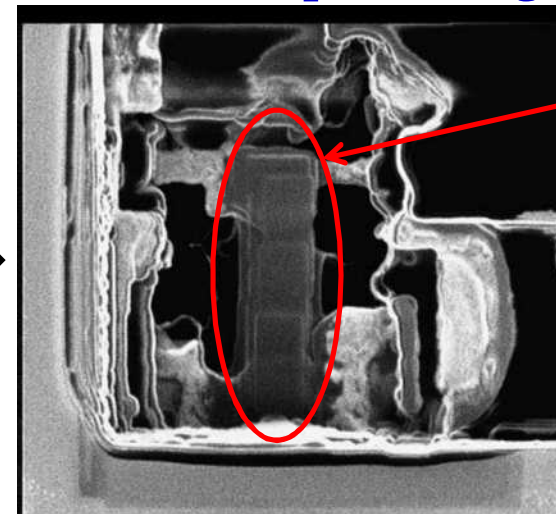
The disconnected input line was connected

with FIB (Focused Ion Beam) processing . ( @VDEC sub-center of Osaka Univ. )

**Exposed location of problem**



**After FIB processing**



Metal

- After FIB processing, the shift register worked correctly.  
→ The 2<sup>nd</sup> production was done with the input registers removed.

# Problem in the 2<sup>nd</sup> production

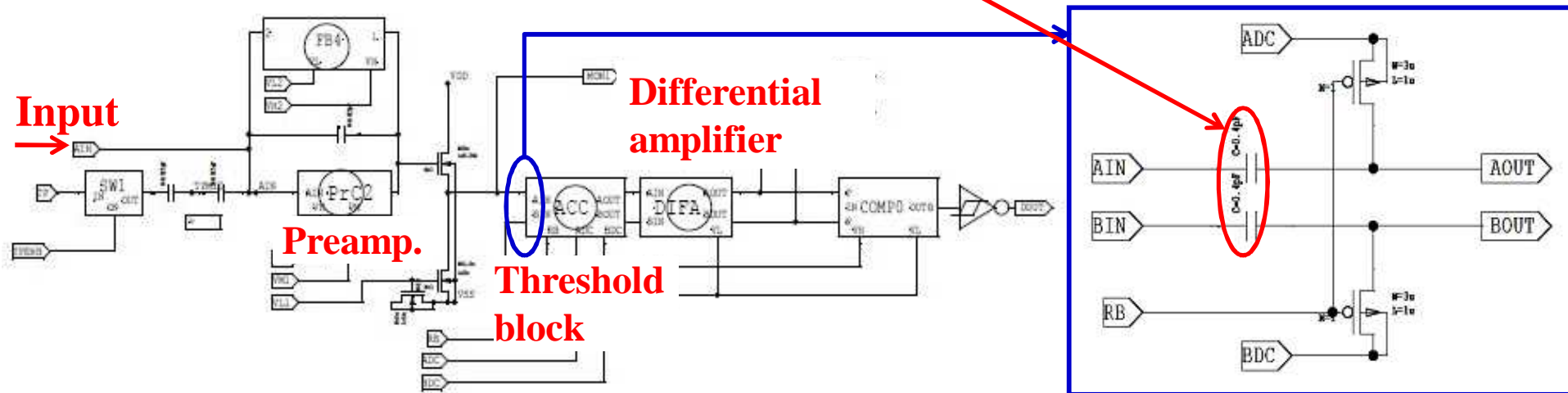
The 2<sup>nd</sup> production of the readout ASIC was done in 2007.

## Problem

- The signal did not pass between pre-amplifier and threshold block.

## Reason

- The layout mask for the MIM capacitor was missing due to a mistake.

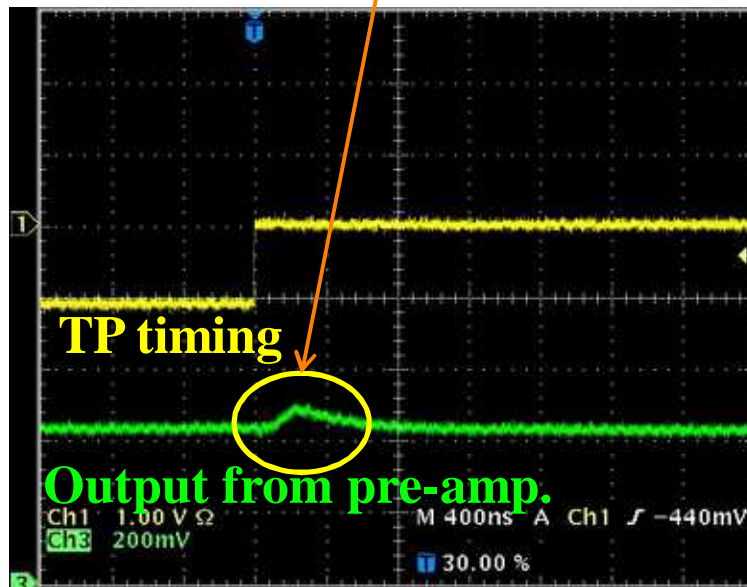
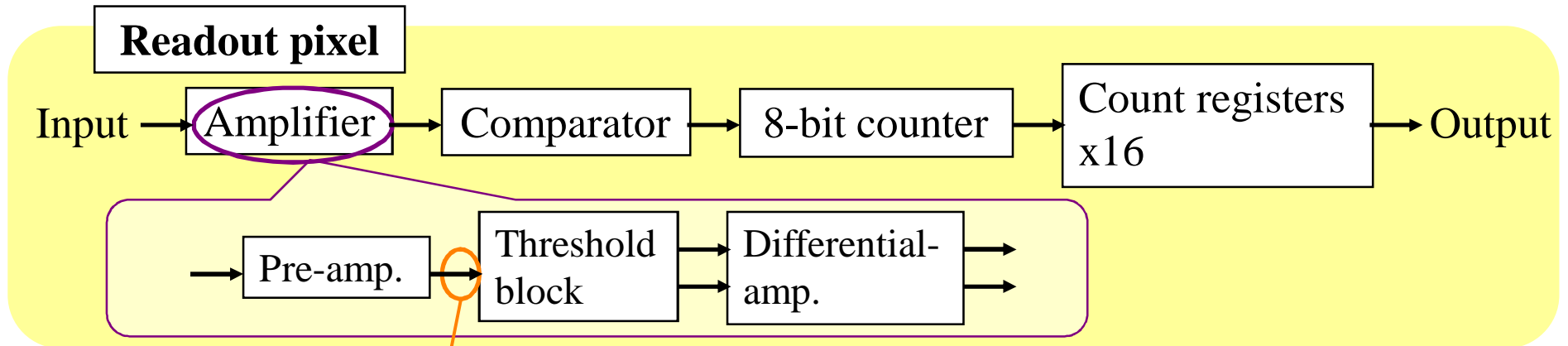


→ The 3<sup>rd</sup> production of the modified readout ASIC was done.

# Response of pre-amplifier

## Operation test of the 3<sup>rd</sup> production

The response of the pre-amplifier was checked.

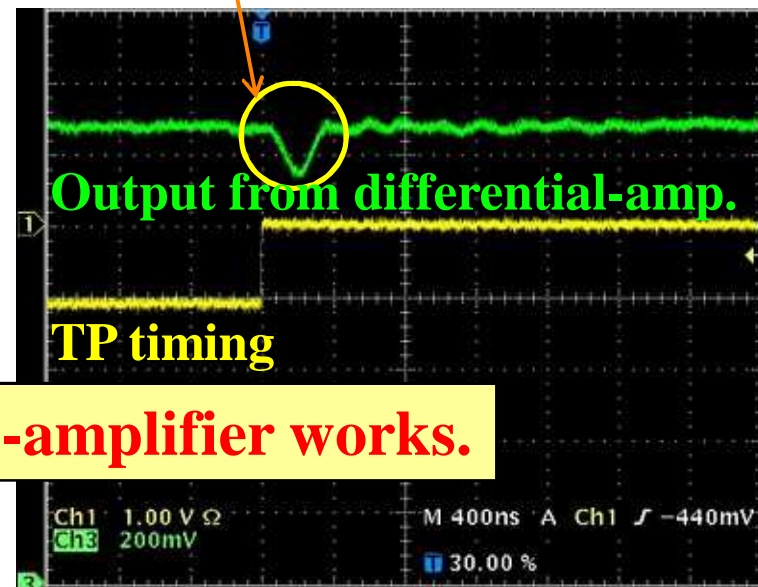
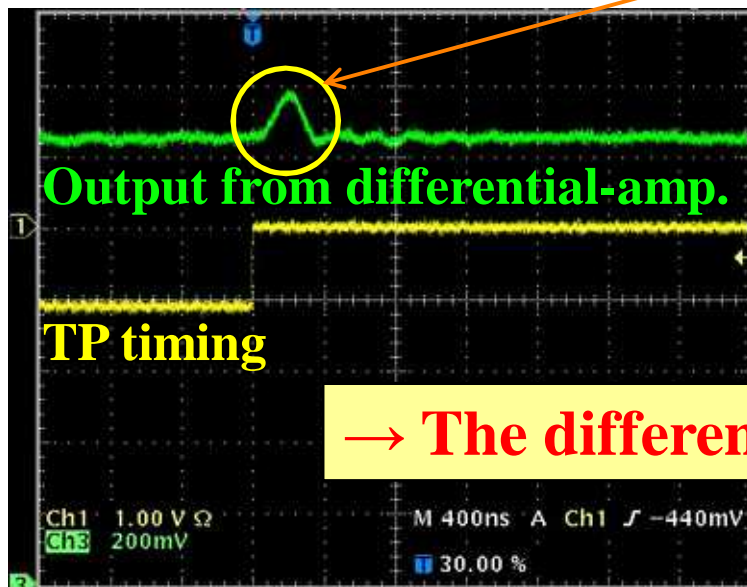
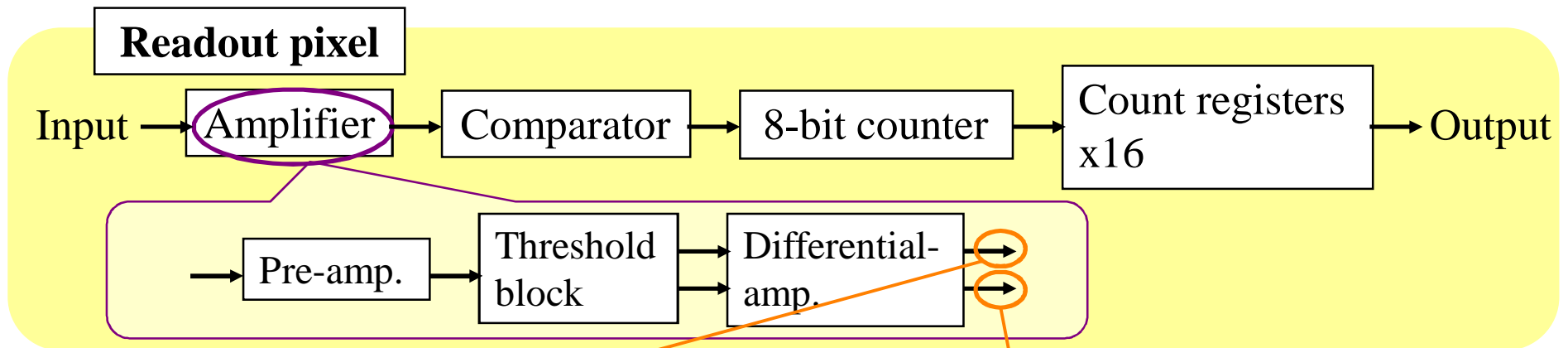


→ The pre-amplifier works.

# Response of differential-amplifier

## Operation test of the 3<sup>rd</sup> production

The response of the differential-amplifier was checked.



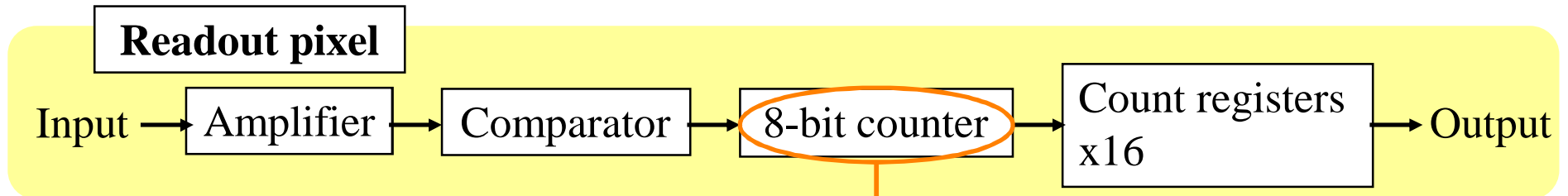
**→ The differential-amplifier works.**



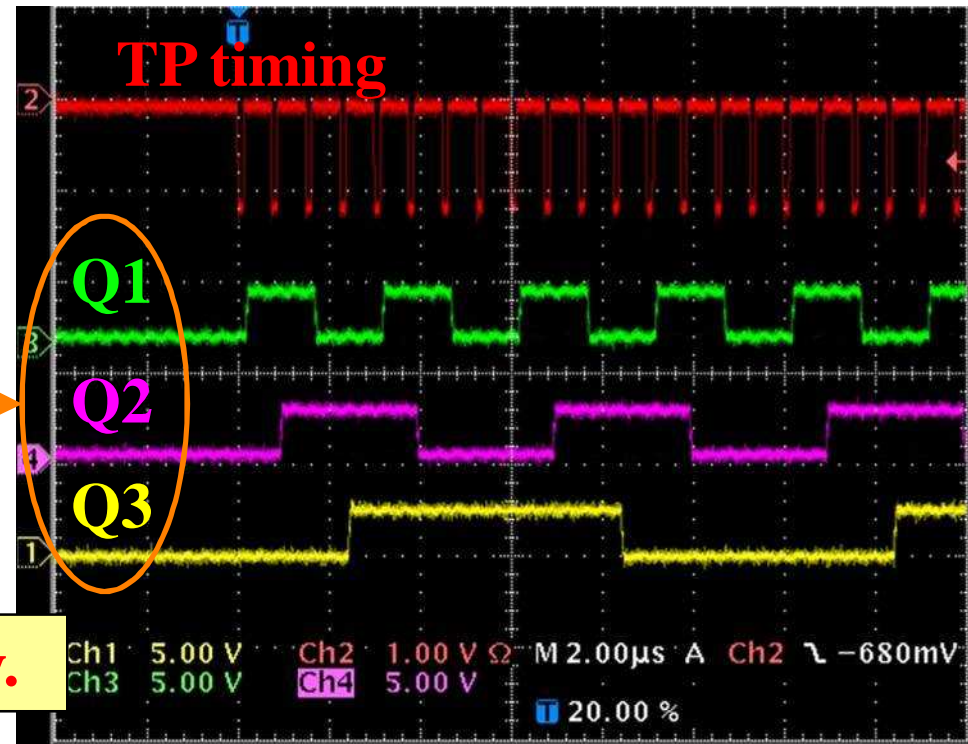
# Response of counter block

## Operation test of the 3<sup>rd</sup> production

The response of the counter was checked.



Gray code is used.



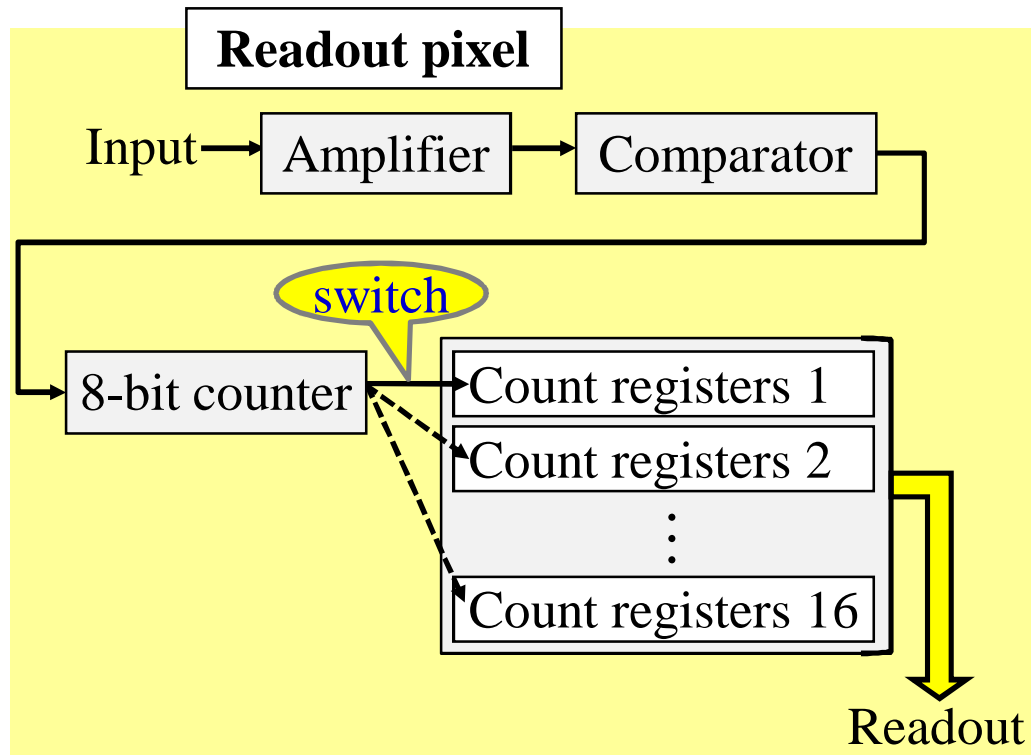
→ The counter works correctly.

# Readout of hit counts

## Operation test of the 3<sup>rd</sup> production

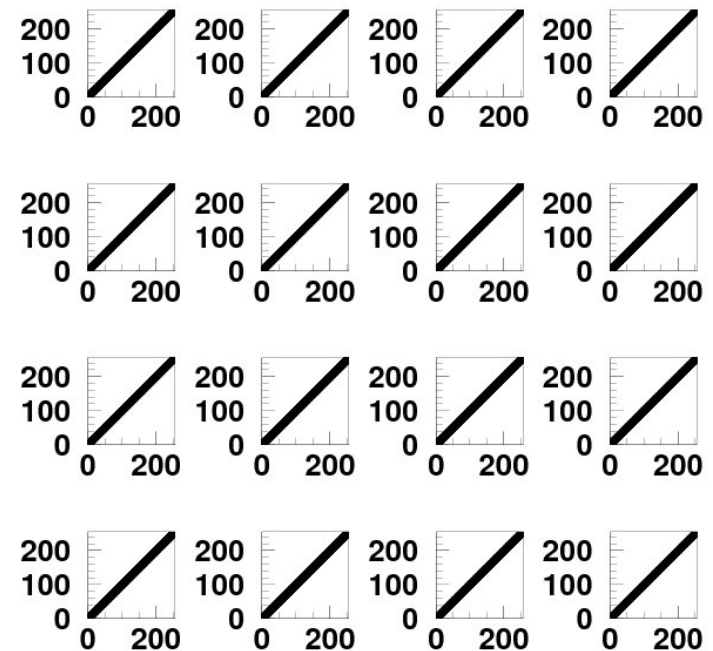
Readout of hit counts was checked.

- The hit count was stored at 2.5MHz hit rate/ (400 $\mu$ m x 400 $\mu$ m) and read out from the count registers.



# of input TP

v.s. # of readout hit counts



**The readout ASIC was confirmed to work correctly as designed.**

### **3. Pair-monitor with SOI technology**

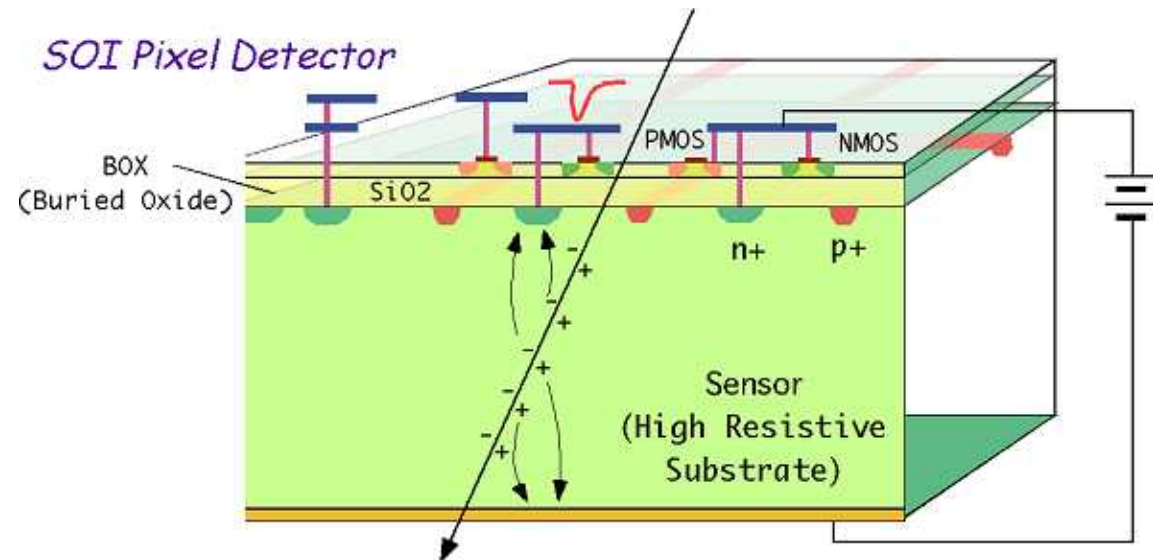
# Pair-monitor with SOI technology

SOI (Silicon On Insulator) technology will be used for the development of the pair-monitor.

## SOI pixel detector

- The sensor and readout electronics are integrated in the SOI substrate. (monolithic)

- High speed
- Lower power
- Thin device
- Low material



The development of the Pair-monitor with SOI technology was started, participating in MPW (Multi Project Wafer) Run at KEK.



# Prototype of SOI chip

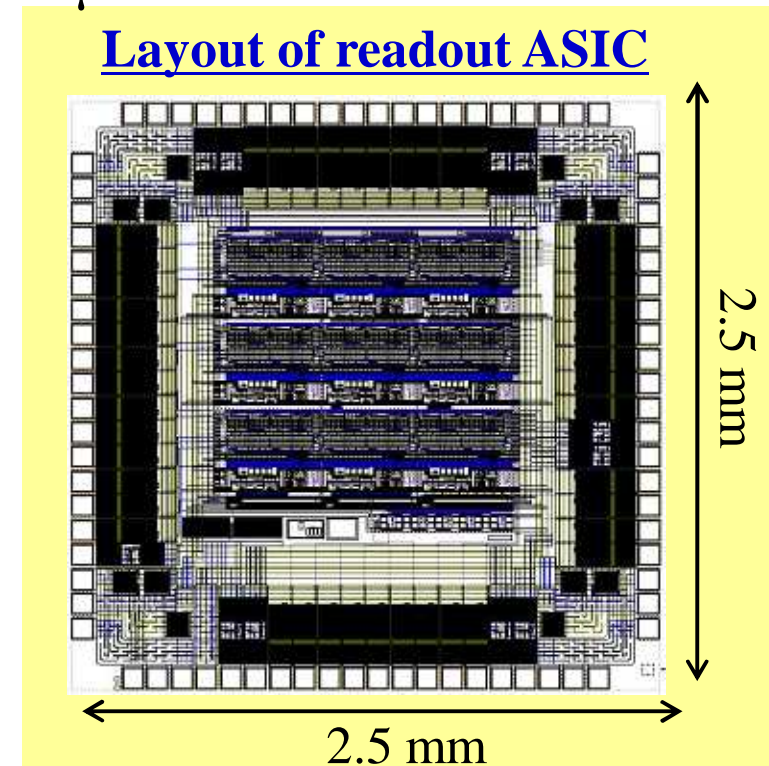
For the next prototype, only the readout ASIC will be developed.

The layout of the readout ASIC was finalized.

## Design of readout ASIC

- Production process : FD - SOI CMOS 0.2  $\mu\text{m}$
- Chip size : 2.5 x 2.5 mm<sup>2</sup>
- # of pixel : 9 ( = 3 x 3 )

The chip will be delivered in Apr., 2009.



## **4. Summary**



## Summary

- Beam profile monitor is necessary for high luminosity.
  - **Pair-monitor**
- The prototype of the readout ASIC was developed.
  - **The chip works correctly as designed.**
  - The chip will be connected with the PIN diode.
- The next readout ASIC will be developed with **SOI** technology.
  - The layout was finalized.
  - The prototype will be delivered in Apr., 2009.

**Thank you for listening!**